

Sub B1
A1 cont
2. [(amended)] The CMP process as claimed in claim 1,

wherein

the auxiliary layer has a layer thickness in the range of 20 to 100 nm.

3. [(amended)] The CMP process as claimed in claim 1,

wherein

the auxiliary layer is used at least partly as a hard mask for the patterning and preceding the etching by dry etching.

4. [(amended)] The CMP process as claimed in claim 1,

wherein

the reaching of the auxiliary layer is detected by an etching stop detection signal during the CMP process.

5. [(amended)] The CMP process as claimed in claim 1,

wherein

an additional wet-chemical cleaning step is carried out at the end of the etching.

6. [(amended)] The CMP process as claimed in claim 1,

wherein

the auxiliary layer is composed of diamond-like carbon, carbon polymers or of porous

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7. ~~(amended)~~ The CMP process as claimed in claim 6,

the auxiliary layer is used in conjunction with a CARL resist as bottom resist.

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[illegible]